Claim 37, line 2, change "electroplating apparatus" to -- reservoir --.

Amend Claims 20, 25, 26, 29, 31, 33, 34, 36 to read:

Sub D1 B1

20. (as amended) An electroplating device for wafer metallization as set forth in claim [19] 39, which further comprises a non-conducting porous separator between said wafer and said counter electrode[, whereby the ionic resistance of said electrolyte is increased].

Sub D3

25. (as amended) A device according to claim [24] 41 in which said distributor is formed with holes at an angle to the flow direction whereby electrolyte emerges from said distributor in the form of multiple submerged jets [contacting] adapted to contact a face of said wafer held in such holder.

B2

26. (as amended) An electroplating device for wafer metallization as set forth in claim [19] 39 which further comprises a [rotatable] distributor in said [apparatus placed] reservoir positioned in front of said [wafer] holder, said distributor being formed with holes at an angle to the flow direction, [the] said distributor being below the level of the electrolyte [being below the face of the wafer] and above said distributor, and means for forcing electrolyte through said distributor in the form of multiple jets contacting the surface of [the] said wafer in said holder and causing rotation of said distributor, [whereby] said jets [serve] serving as an ionic path for the passage of current between said wafer and said counter electrode.

B3 14 16

~~28~~. (as amended) An electroplating device for wafer metallization as set forth in claim [19] ~~39~~ wherein said [wafer] holder is stationary and which further comprises means for rotating said [electroplating apparatus] reservoir.

Sub D4 B4

31. (as amended) An electroplating device for the metallization of wafers for interconnection comprising an electroplating apparatus[,] having a reservoir adapted to contain electrolyte [in said apparatus], a holder for a wafer coated with a thin barrier layer and a thin seed layer of the metal to be electroplated, an assembly of contact pegs on an insulating ring masking the circumferential edge of said wafer and pressing against said wafer, insulating sleeves insulating said pegs from [said] electrolyte[,] in said reservoir except at the points of contact with the wafer, said

contact pegs being spatially distributed over the surface of said wafer to ensure uniform electroplating of the metal over the entire wafer, and means for feeding electrical current from a contact to the center of the wafer and from a plurality of contact points at said counter electrode.

8 ~~33~~. (as amended) An electroplating device for wafer metallization as set forth in claim ~~31~~ 6 [in] which [said] further comprises a pump [pulses] to pulse electrolyte upward against [said] a wafer held in said holder while said wafer is resting on said contact pegs and said insulating ring.

9 ~~34~~. (as amended) An electroplating device for wafer metallization as set forth in claim ~~31~~ 6 which further comprises means for rotating said contact peg assembly and said wafer while said electrolyte is pumped upward against said rotating wafer, said holder supporting said wafer [being supported] so that an active surface of a wafer is exposed to electrolyte and the opposite side of said wafer is protected from said electrolyte.

11 ~~36~~. (as amended) An electroplating device for wafer metallization as set forth in claim ~~31~~ 6 [in] which further comprises means to pulse said pump [pulses] during the electroplating process.

Add the following Claims 39-56:

-- 39. An electroplating device for metallization of wafers for interconnection comprising:
a reservoir for electrolyte,
a holder adapted to hold a wafer above said reservoir,
a counter-electrode in said reservoir,
means for passing current between said counter-electrode and a wafer in said holder, and
a pump for pumping electrolyte from said reservoir against said wafer.

18 ~~40~~. An electroplating device according to claim ~~39~~ 14 which further comprises means for causing relative rotation between said holder and said reservoir.

41. An electroplating device according to claim 39 which further comprises a distributor positioned in said reservoir.

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20 ~~42~~. An electroplating device according to claim ~~41~~ which further comprises means for rotating said distributor relative to said holder.

43. A method of electroplating for the metallization of wafers for interconnection comprising:

providing a reservoir containing a counter-electrode,

providing a holder above said reservoir,

providing a wafer coated with a thin barrier layer and a thin seed layer of the metal to be electroplated over said barrier layer in said holder,

placing an electrolyte containing an electroplated metal in solution in said reservoir and adjusting the plating parameter B^2 of said electrolyte wherein:

$$B^2 = (\rho/\rho_{el})\,(R^2/Wd) < 1$$

where ρ and ρ_{el} are the resistivities of said metal to be electroplated and said electrolyte, respectively, R is the radius of said wafer, W is the thickness of the electroplated metal and d is the distance between said wafer and said counter electrode,

a pump to pump said electrolyte upward against said wafer, and

passing a current between said counter-electrode and said wafer.

22 21

~~44~~. A method according to claim ~~43~~ which further comprises positioning a non-conducting porous separator in said electrolyte above said counter-electrode.

23 21

~~45~~. A method according to claim ~~43~~ wherein the concentration of said electrolyte is such that $B^2 \leq 1$.

24 21

~~46~~. A method according to claim ~~43~~ which further comprises placing leveling agents in solution with said electrolyte to increase charge transfer resistance at a metal/electrolyte interface.

25 21

~~47~~. A method according to claim ~~43~~ wherein the size of said counter-electrode is smaller than the size of said wafer.

20 21

~~48~~. A method according to claim ~~43~~ which further comprises rotating a distributor in said reservoir.

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27 ~~49~~. A method according to claim ~~48~~ 26 in which said distributor is formed with holes at an angle to flow direction whereby electrolyte merges from said distributor in the form of multiple jets submerged in electrolyte directed at a face of said wafer.

28 ~~50~~. A method according to claim ~~49~~ 27 in which said jets cause rotation of said distributor.

29 ~~51~~. A method according to claim ~~49~~ 27 wherein said jets perform said step of passing a current between said counter-electrode and said wafer.

30 ~~52~~. A method according to claim ~~43~~ 21 in which said step of passing current comprises periodically reversing said current, the period of reversed current being smaller than the period of forward current.

31 ~~53~~. A method according to claim ~~43~~ 21 in which said step of pumping said electrolyte comprises pulsing said pump.

32 ~~54~~. A method according to claim ~~43~~ 21 which further comprises causing relative rotation between said wafer and said reservoir.

33 ~~55~~. A method according to claim ~~54~~ 32 in which said reservoir is rotated.

34 ~~56~~. A method according to claim ~~54~~ 32 in which said wafer is rotated. --

REMARKS

The extreme courtesy of the Examiner conducting a telephone interview with the undersigned on February 18, 2000, is acknowledged with appreciation. The Examiner stated he was preparing an Interview Summary; hence no extensive recitation of what was stated is believed necessary.

The new claims and the amendment of prior claims is directed to two points brought out in the interview: